

10/561205

WPO Rec'd PCT/PTO 19 DEC 2005

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masahiro SAKURADA et al.

Application No.: New U.S. National Stage of
PCT/JP04/007349

Filed: December 19, 2005

Docket No.: 126342

For: A METHOD FOR PRODUCING A SINGLE CRYSTAL AND A SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. Relevance of references 4 and 5 is discussed in the present specification.
- 3. References 1-3 were cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information.
- 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- 5. English language Abstracts of the non-English language references are attached hereto.

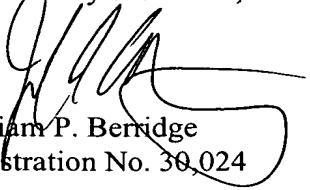
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New U.S. National Stage of PCT/JP04/007349

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6. A computer-generated English language translation of the Japanese Patent Publications has been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and is attached, but has not been reviewed for accuracy.

Respectfully submitted,


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Date: December 19, 2005

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Form PTO-1449 (REV. 8-83)			US Dept. of Commerce PATENT & TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		ATTY DOCKET NO. 126342		APPLICATION NO. New U.S. National Stage of PCT/JP04/007349	
					APPLICANTS Masahiro SAKURADA et al.			
					FILING DATE December 19, 2005			
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS	
	1)	5,919,302	0706/1999	FALSTER et al.				
FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS	
	2)	JP A 2002-057160 w/ abst. & trans	02/22/2002	JAPAN				
	3)	JP A 2000-313691 w/ abst. & trans	11/14/2000	JAPAN				
	4)	JP A 11-147786 w/ abstract & trans	06/02/1999	JAPAN				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)								
	5)	Voronkov, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, Vol. 59, pp. 625-643, 1982						
	6)	Dupret et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No. 9, pp. 1849-1871, 1990						
EXAMINER						DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								